L Number	Hits	Search Text	DB	Time stamp
-	5	("by-pass" or (by adj pass)) with capacitor and ("multi-level" or (multi adj level) or "MLM")	USPAT; JPO; DERWENT	2003/10/05 15:19
-	24	("by-pass" or (by adj pass)) with capacitor and metallization	USPAT; JPO; DERWENT	2003/10/05 15:20
-	426	(etch$4 with first with dielectric) same (deposit$ with electrode) and (etch$4 with second with dielectric) same (deposit$ with (second or top or upper) with electrode)	USPAT; JPO; DERWENT	2003/10/05 15:25
-	4	((etch$4 with first with dielectric) same (deposit$ with electrode) and (etch$4 with second with dielectric) same (deposit$ with (second or top or upper) with electrode)) and adjust$4 with thickness with (dielectric or insulator)	USPAT; JPO; DERWENT	2003/10/05 15:23
-	72	((etch$4 with first with dielectric) same (deposit$ with electrode) and (etch$4 with second with dielectric) same (deposit$ with (second or top or upper) with electrode)) and dielectric adj constant	USPAT; JPO; DERWENT	2003/10/05 15:25
-	44	(((etch$4 with first with dielectric) same (deposit$ with electrode) and (etch$4 with second with dielectric) same (deposit$ with (second or top or upper) with electrode)) and dielectric adj constant) and silicon adj nitride	USPAT; JPO; DERWENT	2003/10/05 15:26
-	16	((((etch$4 with first with dielectric) same (deposit$ with electrode) and (etch$4 with second with dielectric) same (deposit$ with (second or top or upper) with electrode)) and dielectric adj constant) and silicon adj nitride) and angstroms	USPAT; JPO; DERWENT	2003/10/05 15:26
-	106674	"8" and polish$4	USPAT; JPO; DERWENT	2003/10/05 15:26
-	0	((((((etch$4 with first with dielectric) same (deposit$ with electrode) and (etch$4 with second with dielectric) same (deposit$ with (second or top or upper) with electrode)) and dielectric adj constant) and silicon adj nitride) and angstroms) and polish$4) and composite	USPAT; JPO; DERWENT	2003/10/05 15:27
-	13	(((((etch$4 with first with dielectric) same (deposit$ with electrode) and (etch$4 with second with dielectric) same (deposit$ with (second or top or upper) with electrode)) and dielectric adj constant) and silicon adj nitride) and angstroms) and polish$4	USPAT; JPO; DERWENT	2003/10/05 16:07
-	2	"6329666"	USPAT; JPO; DERWENT	2003/10/05 15:28
-	1	((((((etch$4 with first with dielectric) same (deposit$ with electrode) and (etch$4 with second with dielectric) same (deposit$ with (second or top or upper) with electrode)) and dielectric adj constant) and silicon adj nitride) and angstroms) and polish$4) and (multi with level or "MLM")	USPAT; JPO; DERWENT	2003/10/05 16:09
-	1406	(multi with level or "MLM")same (dielectric or insulator)	USPAT; JPO; DERWENT	2003/10/05 16:09
-	264	((multi with level or "MLM")same (dielectric or insulator)) same etch$ with (dielectric or insulator)	USPAT; JPO; DERWENT	2003/10/05 16:10

–	13	(((multi with level or "MLM")same (dielectric or insulator)) same etch$ with (dielectric or insulator)) same deposit$4 with electrode	USPAT; JPO; DERWENT	2003/10/05 16:11
–	9	((((multi with level or "MLM")same (dielectric or insulator)) same etch$ with (dielectric or insulator)) same deposit$4 with electrode) and capacitor	USPAT; JPO; DERWENT	2003/10/05 16:18
–	149	VLSI and ("by-pass" or by adj pass)	USPAT; JPO; DERWENT	2003/10/05 16:19
–	0	(VLSI and ("by-pass" or by adj pass)) and electrode and MIM	USPAT; JPO; DERWENT	2003/10/05 16:20
–	26	(VLSI and ("by-pass" or by adj pass)) and electrode	USPAT; JPO; DERWENT	2003/10/05 16:21
–	0	MIM and (by adj pass) and MLM	USPAT; JPO; DERWENT	2003/10/05 16:21
–	0	MIM and (by adj pass) and multi adj layer adj metallization	USPAT; JPO; DERWENT	2003/10/05 16:21
–	0	(by adj pass) and multi adj layer adj metallization	USPAT; JPO; DERWENT	2003/10/05 16:47
–	5	"6271596"	USPAT; JPO; DERWENT	2003/10/05 17:09
–	18	"MIM" same multi with layer with metal	USPAT; JPO; DERWENT	2003/10/05 17:09
–	19	"MIM" same multi with layer with metal$7	USPAT; JPO; DERWENT	2003/10/05 17:09
–	8	("MIM" same multi with layer with metal$7) and etch$4 with dielectric	USPAT; JPO; DERWENT	2003/10/05 17:09
–	8	("MIM" same multi with layer with metal$7) and etch$4 with (dielectric or insulator)	USPAT; JPO; DERWENT	2003/10/05 17:10
–	5	(("MIM" same multi with layer with metal$7) and etch$4 with (dielectric or insulator)) and electrode	USPAT; JPO; DERWENT	2003/10/05 17:16
–	0	MIM same (multi with level) and parallel with dishing	USPAT; JPO; DERWENT	2003/10/05 17:17
–	0	metal same (multi with level) and parallel with dishing	USPAT; JPO; DERWENT	2003/10/05 17:17
–	0	MIM same (multi with level) and dishing	USPAT; JPO; DERWENT	2003/10/05 17:17
–	10	MIM same (multi with level)	USPAT; JPO; DERWENT	2003/10/05 17:18
–	340	MIM same wiring	USPAT; JPO; DERWENT	2003/10/05 17:18
–	0	(MIM same wiring) and parallel with dishing	USPAT; JPO; DERWENT	2003/10/05 17:18
–	0	(MIM same wiring) and parallel and dishing	USPAT; JPO; DERWENT	2003/10/05 17:19
–	0	(MIM same wiring) and dishing	USPAT; JPO; DERWENT	2003/10/05 17:19
–	128645	(MIM same wiring) electrode and etch$	USPAT; JPO; DERWENT	2003/10/05 17:19

-	142	(MIM same wiring) and electrode and etch$4	USPAT; JPO; DERWENT	2003/10/05 17:19
-	116	((MIM same wiring) and electrode and etch$4) and (wiring with electrode)	USPAT; JPO; DERWENT	2003/10/05 17:19
-	92	(((MIM same wiring) and electrode and etch$4) and (wiring with electrode)) and (insulator or dielectric)	USPAT; JPO; DERWENT	2003/10/05 17:21
-	1	((((MIM same wiring) and electrode and etch$4) and (wiring with electrode)) and (insulator or dielectric)) and (multi adj layer with metal$7)	USPAT; JPO; DERWENT	2003/10/05 17:20
-	4	((((MIM same wiring) and electrode and etch$4) and (wiring with electrode)) and (insulator or dielectric)) and (multi with layer with metal$7)	USPAT; JPO; DERWENT	2003/10/05 17:20
-	0	((((MIM same wiring) and electrode and etch$4) and (wiring with electrode)) and (insulator or dielectric)) and "MLMD"	USPAT; JPO; DERWENT	2003/10/05 17:22
-	0	(multi with layer with metallization with device) and MIM	USPAT; JPO; DERWENT	2003/10/05 17:22
-	1	(multi with layer with metallization with device) and metal with capacitor	USPAT; JPO; DERWENT	2003/10/05 17:22
-	124	multi with layer with metallization with device	USPAT; JPO; DERWENT	2003/10/05 17:37
-	3	("5591677" | "6093637" | "6239026").PN.	USPAT	2003/10/05 17:36
-	0	(("5591677" | "6093637" | "6239026").PN.) and capacitor	USPAT; JPO; DERWENT	2003/10/05 17:36
-	3	multi with layer with metallization and MIM	USPAT; JPO; DERWENT	2003/10/05 17:38
-	157	metallization and MIM	USPAT; JPO; DERWENT	2003/10/05 17:40
-	89	metallization with layer and MIM	USPAT; JPO; DERWENT	2003/10/05 17:40
-	30	(metallization with layer and MIM) and etch$4 with dielectric	USPAT; JPO; DERWENT	2003/10/05 17:40
-	23	((metallization with layer and MIM) and etch$4 with dielectric) and electrode	USPAT; JPO; DERWENT	2003/10/05 17:42
-	20	(((metallization with layer and MIM) and etch$4 with dielectric) and electrode) and (lines or wiring)	USPAT; JPO; DERWENT	2003/10/05 17:43
-	36	"multi-layer" adj metallization and capacitor	USPAT; JPO; DERWENT	2003/10/05 17:51
-	9	("multi-layer" adj metallization and capacitor) and etch$4 with dielectric	USPAT; JPO; DERWENT	2003/10/05 17:48
-	507	((lower or bottom or first) adj electrode) same signal adj lines	USPAT; JPO; DERWENT	2003/10/05 17:51
-	84	(((lower or bottom or first) adj electrode) same signal adj lines) same parallel	USPAT; JPO; DERWENT	2003/10/05 17:49
-	0	(((((lower or bottom or first) adj electrode) same signal adj lines) same parallel) and (insulator or dielectric)) and "high-k"	USPAT; JPO; DERWENT	2003/10/05 17:49
-	0	(((((lower or bottom or first) adj electrode) same signal adj lines) same parallel) and (insulator or dielectric)) and CMP	USPAT; JPO; DERWENT	2003/10/05 17:50

-	48	((((lower or bottom or first) adj electrode) same signal adj lines) same parallel) and (insulator or dielectric)	USPAT; JPO; DERWENT	2003/10/05 17:50
-	8745	((lower or bottom or first) adj electrode) same lines	USPAT; JPO; DERWENT	2003/10/05 17:51
-	2	(((lower or bottom or first) adj electrode) same lines) and "multi-layer" adj metallization	USPAT; JPO; DERWENT	2003/10/05 17:52
-	5	"high-k" with MIM	USPAT; JPO; DERWENT	2003/10/05 17:54
-	2	("high-k" with MIM) and CMP	USPAT; JPO; DERWENT	2003/10/05 18:11
-	2	VLSI with "multi-layer" adj metallization	USPAT; JPO; DERWENT	2003/10/05 18:11
-	4	VLSI same "multi-layer" adj metallization	USPAT; JPO; DERWENT	2003/10/05 18:12
-	2	"multi-layer" adj metallization and MIM	USPAT; JPO; DERWENT	2003/10/05 18:13
-	10	"MLM" and MIM	USPAT; JPO; DERWENT	2003/10/05 18:14
-	147	multi with metal and MIM	USPAT; JPO; DERWENT	2003/10/05 18:14
-	72	(multi with metal and MIM) and dielectric	USPAT; JPO; DERWENT	2003/10/05 18:14
-	67	((multi with metal and MIM) and dielectric) and electrode	USPAT; JPO; DERWENT	2003/10/05 18:14
-	11	(((multi with metal and MIM) and dielectric) and electrode) and CMP	USPAT; JPO; DERWENT	2003/10/05 18:18
-	102	MIM and VLSI	USPAT; JPO; DERWENT	2003/10/05 18:19
-	63	(MIM and VLSI) and dielectric	USPAT; JPO; DERWENT	2003/10/05 18:19
-	15	((MIM and VLSI) and dielectric) and CMP	USPAT; JPO; DERWENT	2003/10/05 18:19
-	13	(((MIM and VLSI) and dielectric) and CMP) and electrode	USPAT; JPO; DERWENT	2003/10/05 18:36
-	5	("5162258" | "5812364" | "5913126" | "5918135" | "5920775").PN.	USPAT	2003/10/05 18:35
-	5	(("5162258" | "5812364" | "5913126" | "5918135" | "5920775").PN.) and MIM	USPAT; JPO; DERWENT	2003/10/05 18:36
-	1	((("5162258" | "5812364" | "5913126" | "5918135" | "5920775").PN.) and MIM) and "multi-layer"	USPAT; JPO; DERWENT	2003/10/05 18:38
-	0	"multi-layer" with metallization and capacitro	USPAT; JPO; DERWENT	2003/10/05 18:38
-	126	"multi-layer" with metallization and capacitor	USPAT; JPO; DERWENT	2003/10/05 18:38
-	94	("multi-layer" with metallization and capacitor) and dielectric	USPAT; JPO; DERWENT	2003/10/05 18:39
-	35	(("multi-layer" with metallization and capacitor) and dielectric) and electrode with etch$	USPAT; JPO; DERWENT	2003/10/05 18:39

-	2	((("multi-layer" with metallization and capacitor) and dielectric) and electrode with etch$) and CMP	USPAT; JPO; DERWENT	2003/10/05 18:41
-	0	(((("multi-layer" with metallization and capacitor) and dielectric) and electrode with etch$) and CMP) and dielectric adj constant	USPAT; JPO; DERWENT	2003/10/05 18:41
-	2	("6077742" | "6184081").PN.	USPAT	2003/10/05 18:41
-	2	(("6077742" | "6184081").PN.) and CMP	USPAT; JPO; DERWENT	2003/10/05 18:42
-	0	(("6077742" | "6184081").PN.) and MIM	USPAT; JPO; DERWENT	2003/10/05 18:48
-	8	"6124199"	USPAT; JPO; DERWENT	2003/10/05 18:53
-	99	(multi with level with metallization) and capacitor	USPAT; JPO; DERWENT	2003/10/05 18:53
-	89	((multi with level with metallization) and capacitor) and (insulator or dielectric)	USPAT; JPO; DERWENT	2003/10/05 18:53
-	81	(((multi with level with metallization) and capacitor) and (insulator or dielectric)) and etch$4	USPAT; JPO; DERWENT	2003/10/05 18:53
-	44	((((multi with level with metallization) and capacitor) and (insulator or dielectric)) and etch$4) and electrode	USPAT; JPO; DERWENT	2003/10/05 18:53
-	9	("5315141" | "5323037" | "5479316" | "5686339" | "5753558" | "5792687" | "5926359" | "6174770" | "6376874").PN.	USPAT	2003/10/05 19:02
-	8	("4335505" | "4786612" | "5068694" | "5366920" | "5436477" | "5439840" | "5440174" | "5670808").PN.	USPAT	2003/10/05 19:17